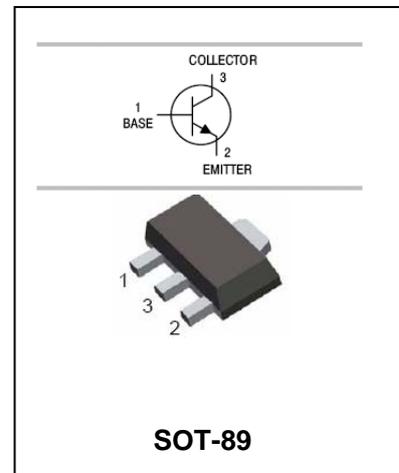


NPN Silicon Epitaxial Planar Transistor

2SC5964

FEATURES

- Adoption of MBIT process.
- High current capacitance.
- Low collector-to-emitter saturation voltage.
- High-speed switching.



APPLICATIONS

- DC / DC converter, relay drivers, lamp drivers, motor drivers, flash.

ORDERING INFORMATION

Type No.	Marking	Package Code
2SC5964		SOT-89

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Units	
V _{CB0}	Collector-Base Voltage	100	V	
V _{CES}	Collector-Emitter Voltage	100	V	
V _{CEO}	Collector-Emitter Voltage	50	V	
V _{EBO}	Emitter-Base Voltage	6	V	
I _C	Collector Current -Continuous	3	A	
I _B	Base Current	600	mA	
P _C	Collector Dissipation	Mounted on a ceramic board (250mm ² *0.8m)	1.3	W
		T _c =25°C	3.5	
T _J	Junction Temperature	150	°C	
T _{stg}	Storage Temperature	-55 to +150	°C	



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ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_B=0$	100			V
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$I_C=100\mu A, R_{BE}=0$	100			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, R_{BE}=\infty$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=40V, I_E=0$			1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4V, I_C=0$			1	μA
DC current gain	h_{FE}	$V_{CE}=2V, I_C=100mA$	200		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=1A, I_B=50mA$ $I_C=2A, I_B=100mA$		100 190	150 290	mV
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$V_{CE}=2V, I_B=100mA$		0.94	1.2	V
Transition frequency	f_T	$V_{CE}=10V, I_C=500mA$		380		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$		13		pF

CLASSIFICATION OF h_{FE}

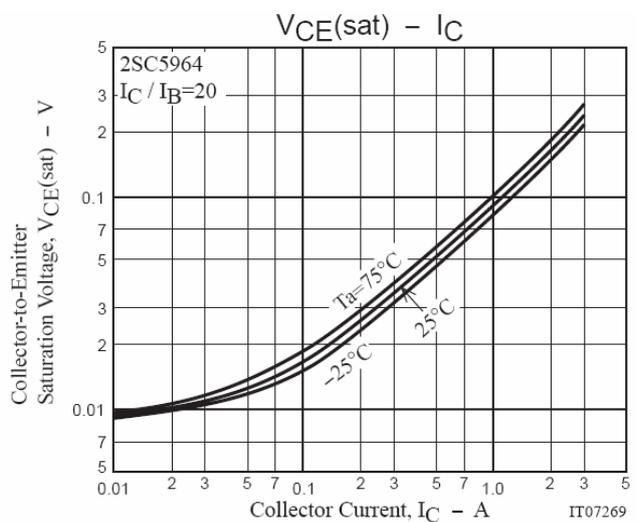
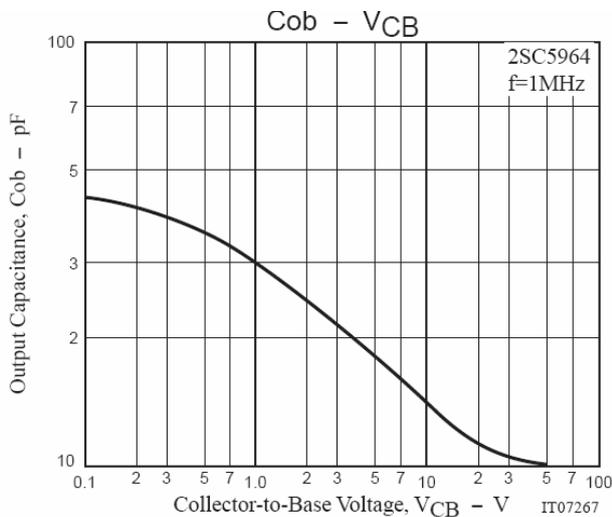
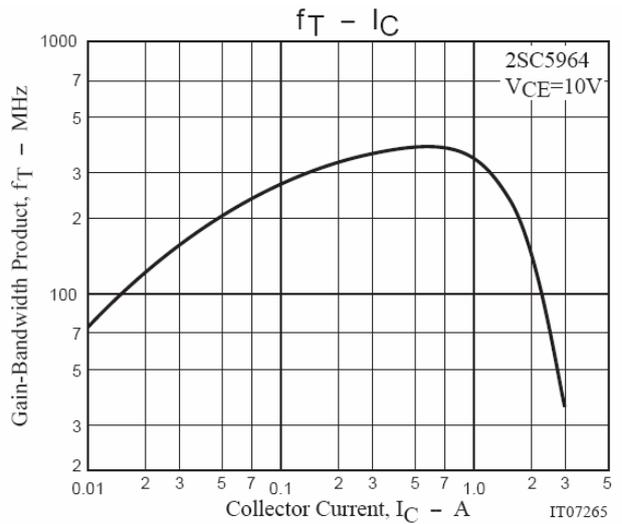
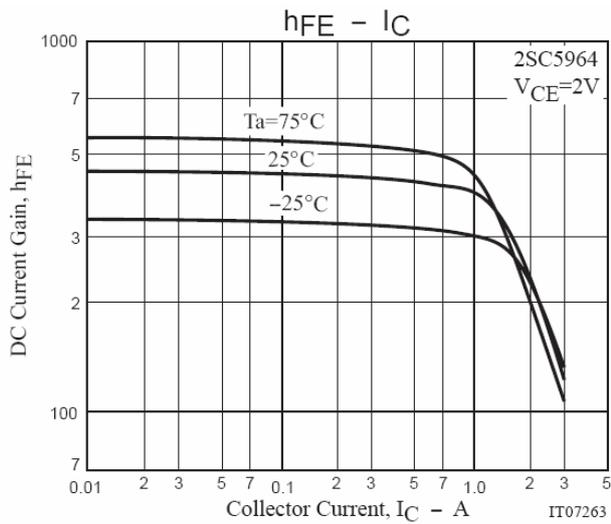
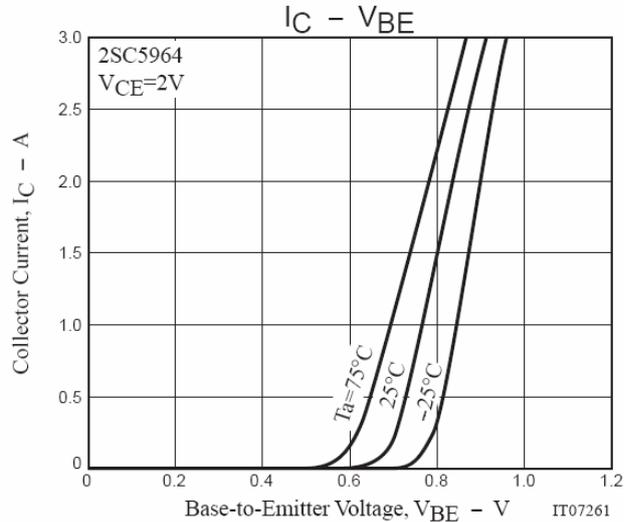
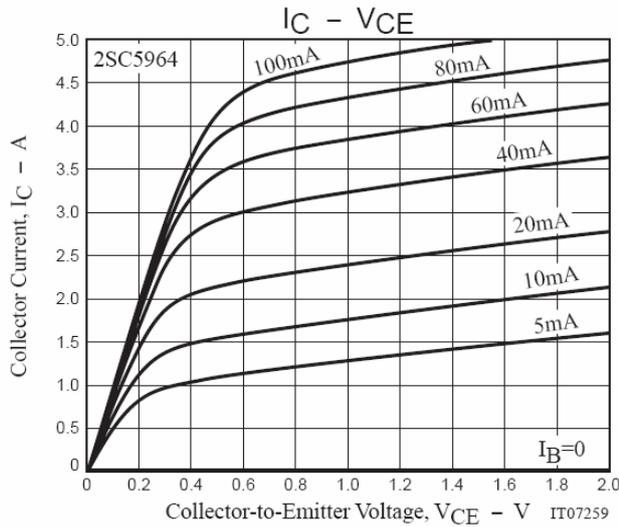
Rank	O	Y
Range	100-200	160-320
MARKING	GO	GY



NPN Silicon Epitaxial Planar Transistor

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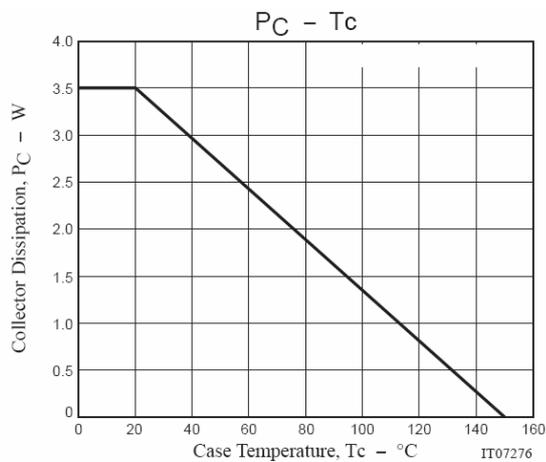
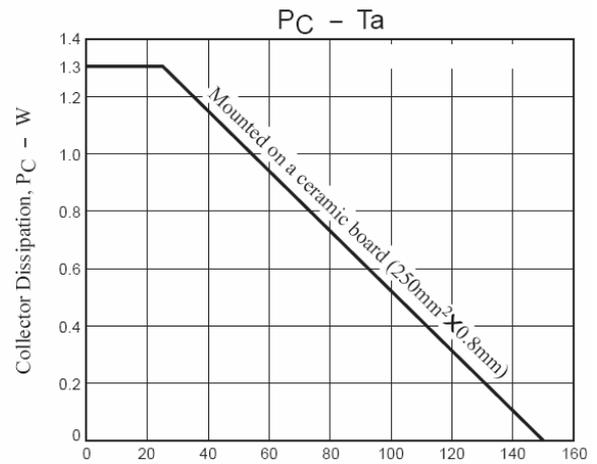
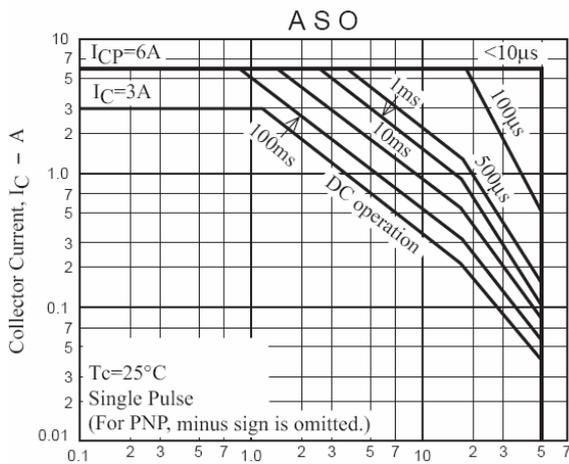
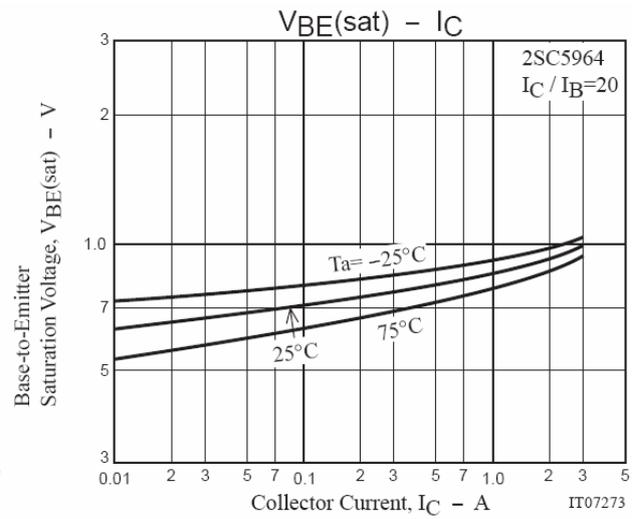
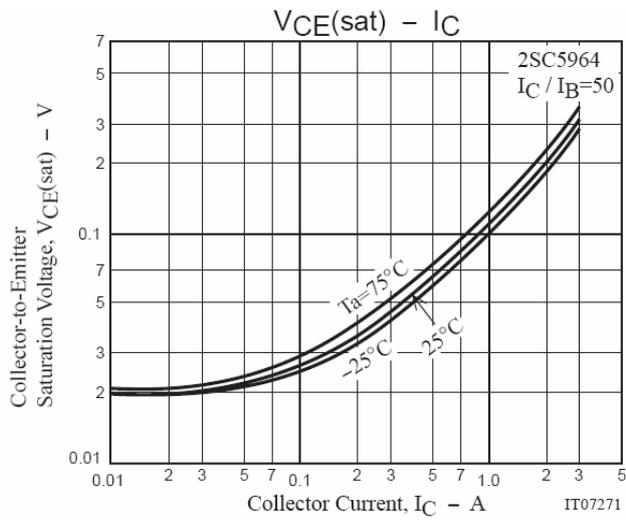
TYPICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified





NPN Silicon Epitaxial Planar Transistor

2SC5964



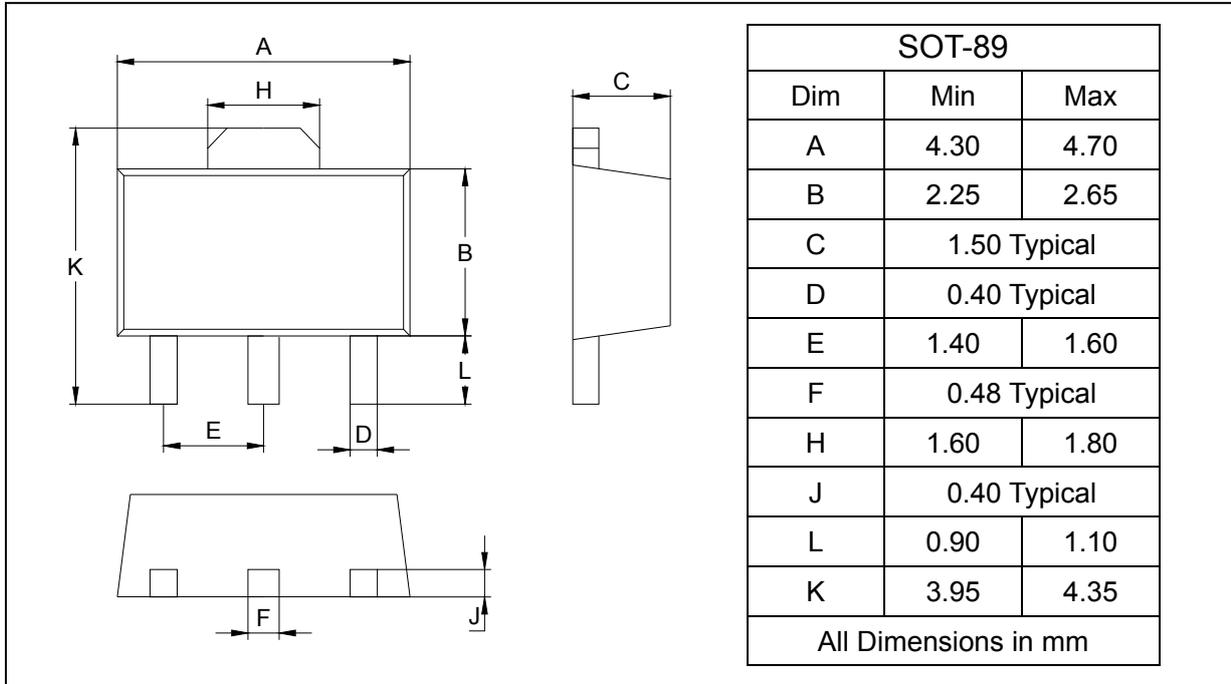
NPN Silicon Epitaxial Planar Transistor

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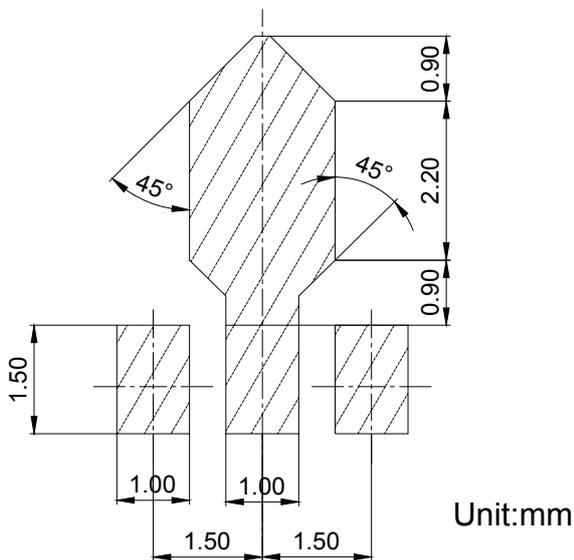
PACKAGE OUTLINE

Plastic surface mounted package

SOT-89



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
2SC5964	SOT-89	1000/Tape&Reel